

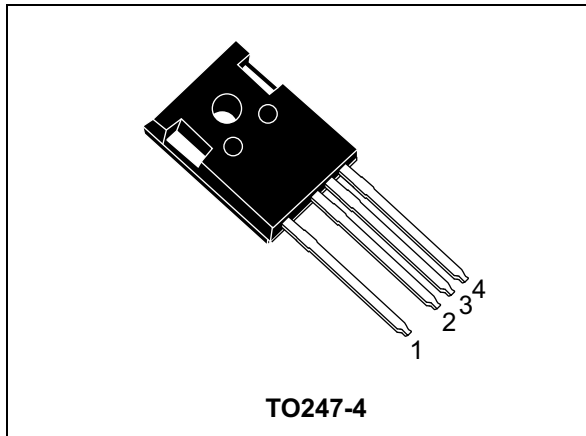


**THE DATASHEET OF  
STW56N65M2-4**

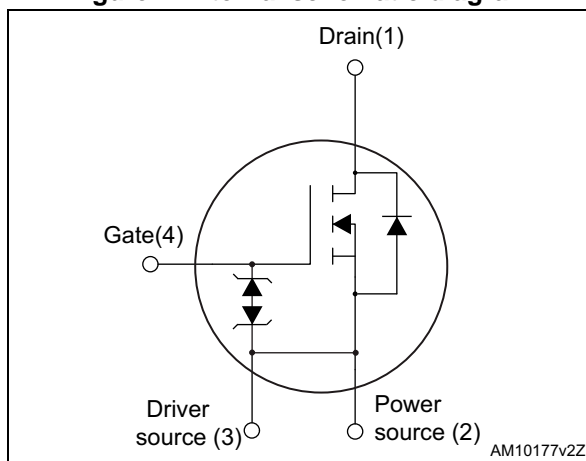


## N-channel 650 V, 0.049 $\Omega$ typ., 49 A MDmesh™ M2 Power MOSFET in a TO247-4 package

Datasheet - production data



**Figure 1. Internal schematic diagram**



### Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STW56N65M2-4	650 V	0.062 $\Omega$	49 A

- Excellent switching performance thanks to the extra driving source pin
- Extremely low gate charge
- Excellent output capacitance (C<sub>oss</sub>) profile
- 100% avalanche tested
- Zener-protected

### Applications

- Switching applications

### Description

This device is an N-channel Power MOSFET developed using MDmesh™ M2 technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance and optimized switching characteristics, rendering it suitable for the most demanding high efficiency converters.

**Table 1. Device summary**

Order code	Marking	Package	Packaging
STW56N65M2-4	56N65M2	TO247-4	Tube

# Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate- source voltage	$\pm 25$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	49	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	31	A
$I_{DM}^{(1)}$	Drain current (pulsed)	196	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	358	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET $dv/dt$ ruggedness	50	V/ns
$T_{stg}$	Storage temperature	- 55 to 150	$^\circ\text{C}$
$T_j$	Max. operating junction temperature	150	$^\circ\text{C}$

1. Pulse width limited by safe operating area
2.  $I_{SD} \leq 49\text{ A}$ ,  $di/dt = 400\text{ A}/\mu\text{s}$ ,  $V_{DS(\text{peak})} < V_{(BR)DSS}$ ,  $V_{DD} = 400\text{ V}$
3.  $V_{DS} \leq 520\text{ V}$

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-amb}$	Thermal resistance junction-ambient max	50	$^\circ\text{C}/\text{W}$
$R_{thj-case}$	Thermal resistance junction-case max	0.35	$^\circ\text{C}/\text{W}$

**Table 4. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Max current during repetitive or single pulse avalanche (pulse width limited by $T_{JMAX}$ )	3.5	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	1300	mJ

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 5. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	650			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 650\text{ V}$ $V_{DS} = 650\text{ V}$ , $T_C = 125\text{ °C}$			1 100	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 25\text{ V}$			$\pm 10$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 24.5\text{ A}$		0.049	0.062	$\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	3900	-	pF
$C_{oss}$	Output capacitance		-	160	-	pF
$C_{riss}$	Reverse transfer capacitance		-	2.8	-	pF
$C_{o(er)}^{(1)}$	Equivalent Output Capacitance	$V_{GS} = 0$ , $V_{DS} = 0\text{ to }520\text{ V}$	-	838	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	4.6	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 520\text{ V}$ , $I_D = 49\text{ A}$ , $V_{GS} = 10\text{ V}$ , (see <a href="#">Figure 15</a> )	-	93	-	nC
$Q_{gs}$	Gate-source charge		-	16	-	nC
$Q_{gd}$	Gate-drain charge		-	40	-	nC

1.  $C_{oss}$  eq. is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

Table 7. Switching times

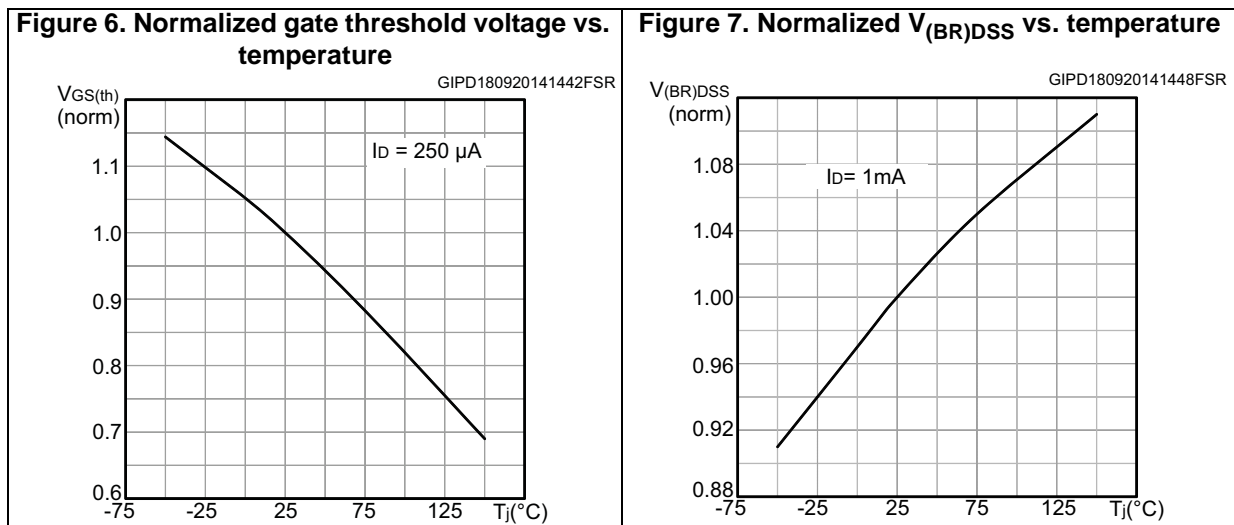
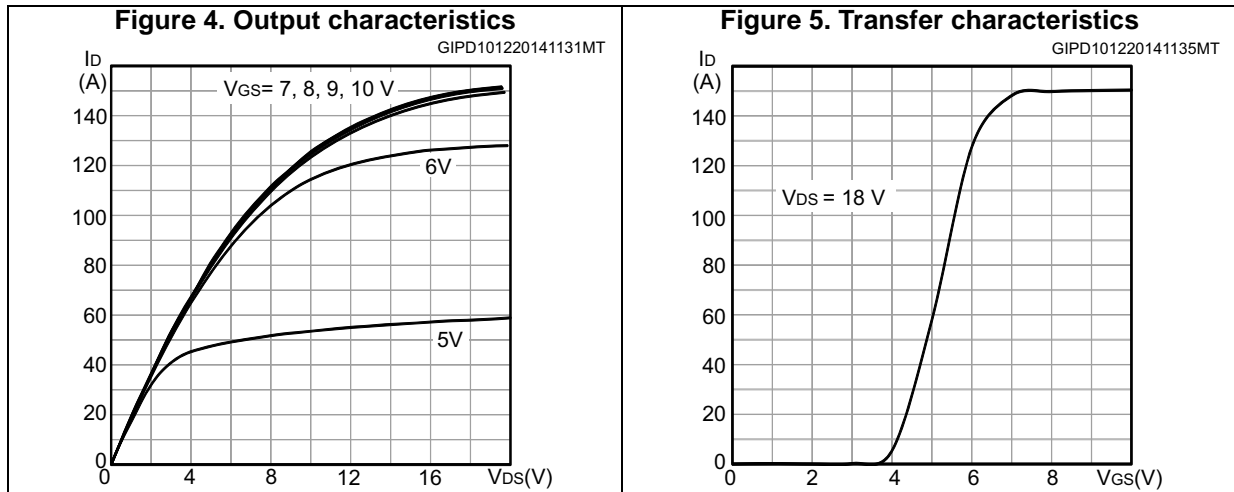
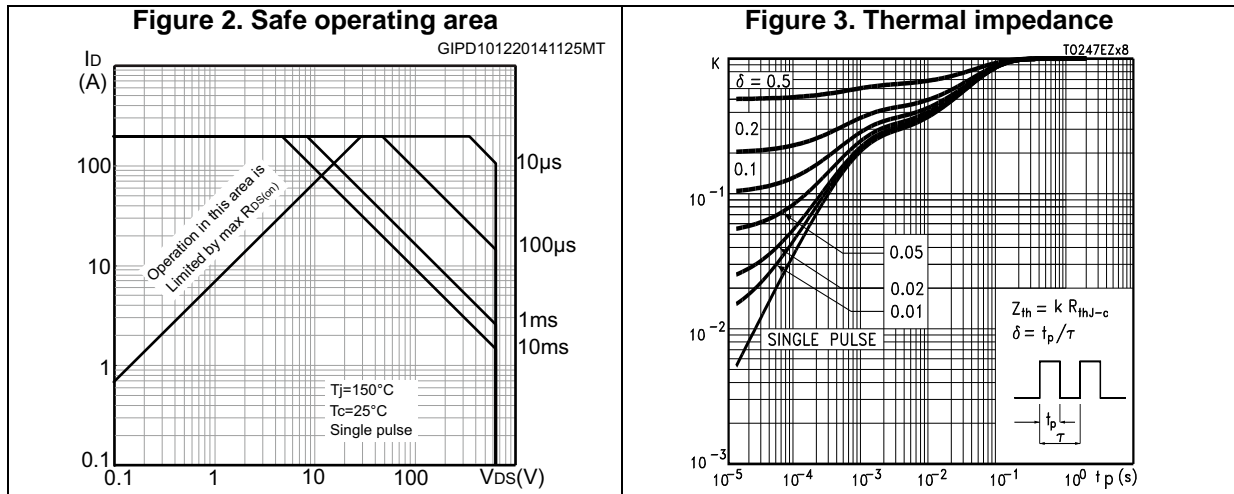
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 325 \text{ V}$ , $I_D = 24.5 \text{ A}$ , $R_G = 4.7 \text{ } \Omega$ , $V_{GS} = 10 \text{ V}$ (see <a href="#">Figure 16</a> and <a href="#">Figure 19</a> )	-	19	-	ns
$t_r$	Rise time		-	27.5	-	ns
$t_{d(off)}$	Turn-off delay time		-	146	-	ns
$t_f$	Fall time		-	13	-	ns

Table 8. Source drain diode

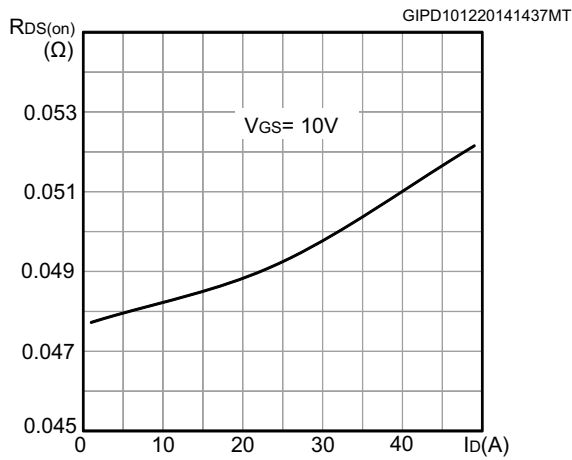
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		49	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		196	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 49 \text{ A}$ , $V_{GS} = 0$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 49 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ (see <a href="#">Figure 16</a> )	-	554		ns
$Q_{rr}$	Reverse recovery charge		-	13.5		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	49.5		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 49 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ , $T_j = 150 \text{ }^\circ\text{C}$ (see <a href="#">Figure 19</a> )	-	688		ns
$Q_{rr}$	Reverse recovery charge		-	18		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	52		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

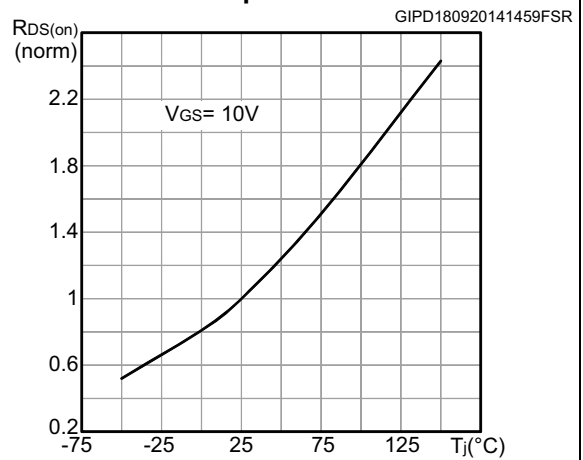
## 2.1 Electrical characteristics (curves)



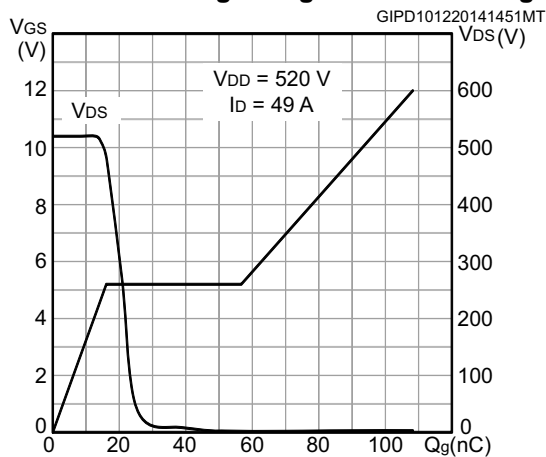
**Figure 8. Static drain-source on-resistance**



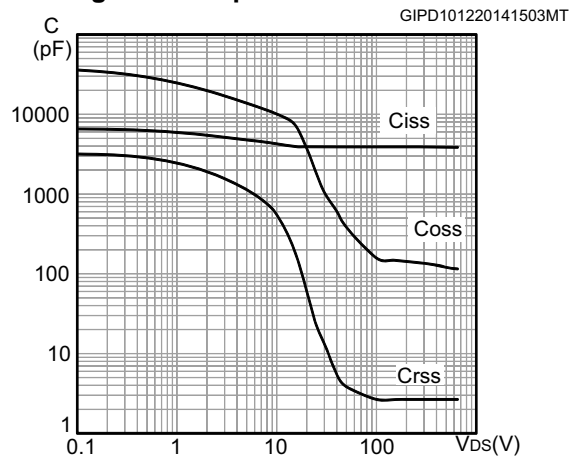
**Figure 9. Normalized on-resistance vs. temperature**



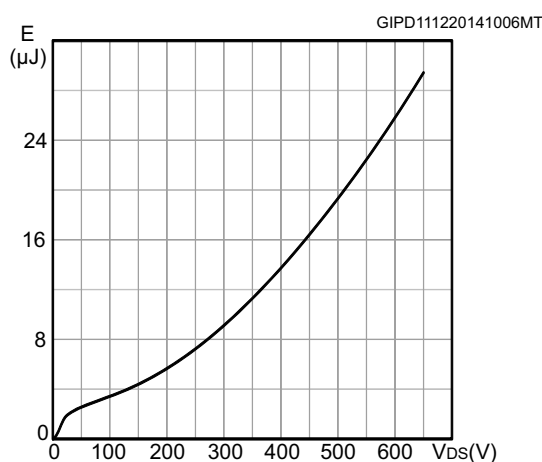
**Figure 10. Gate charge vs. gate-source voltage**



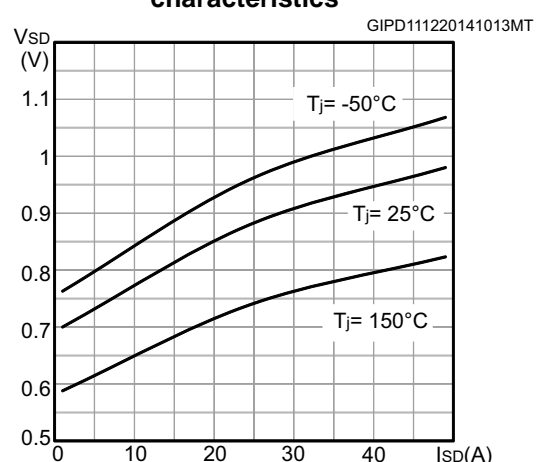
**Figure 11. Capacitance variations**



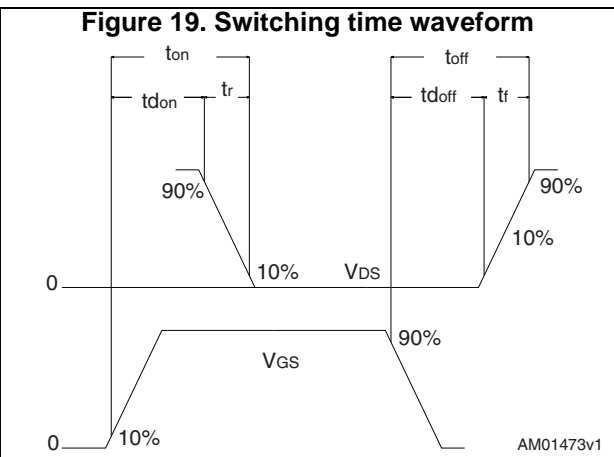
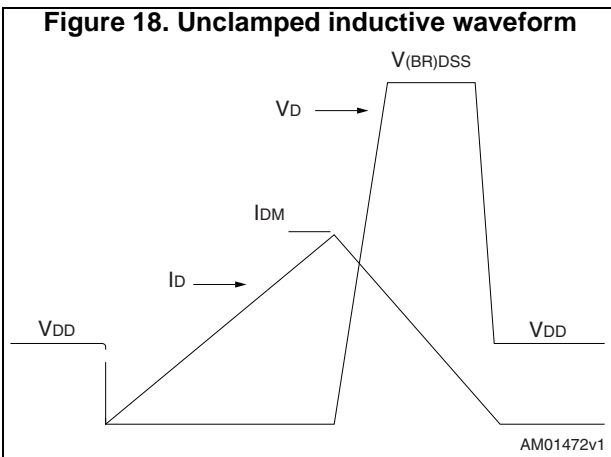
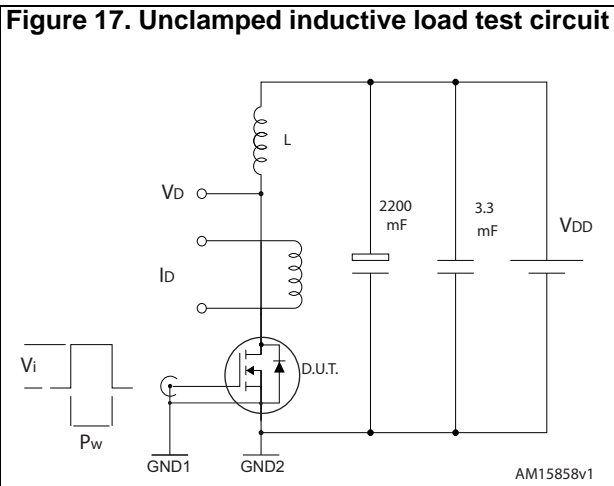
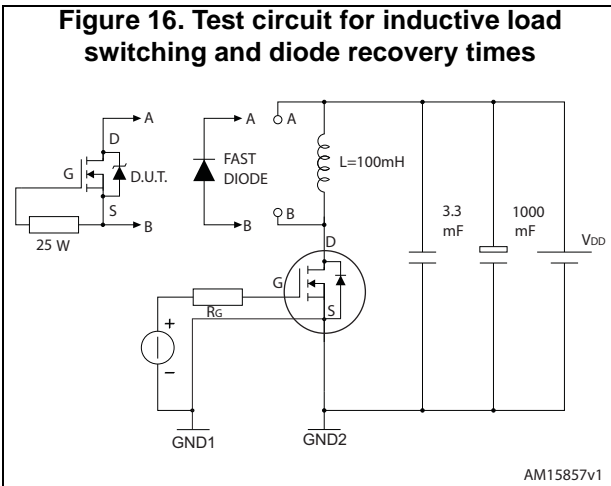
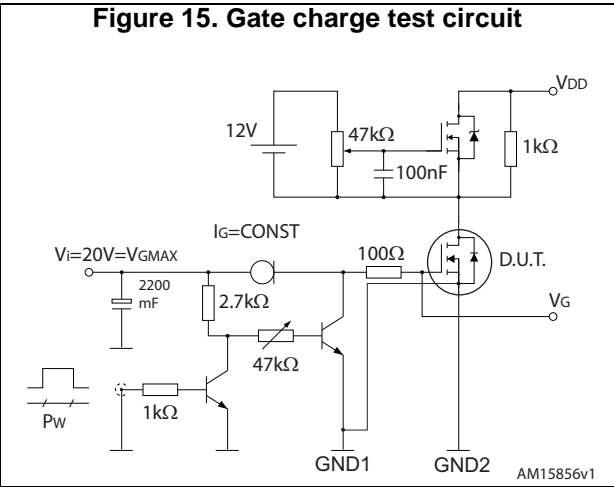
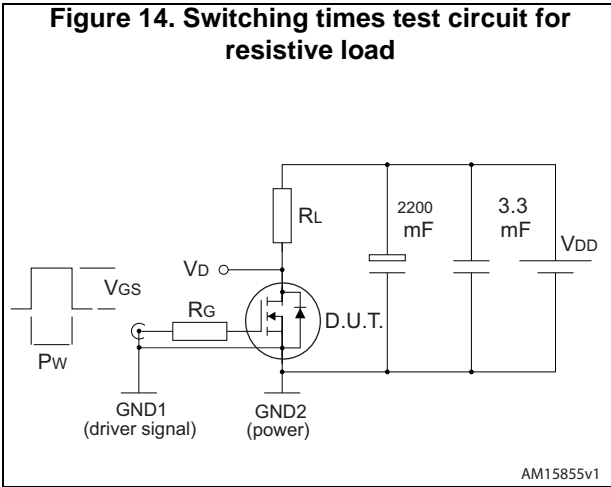
**Figure 12. Output capacitance stored energy**



**Figure 13. Source-drain diode forward characteristics**



### 3 Test circuits



## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 4.1 TO247-4, STW56N65M2-4

Figure 20. TO247-4 drawing

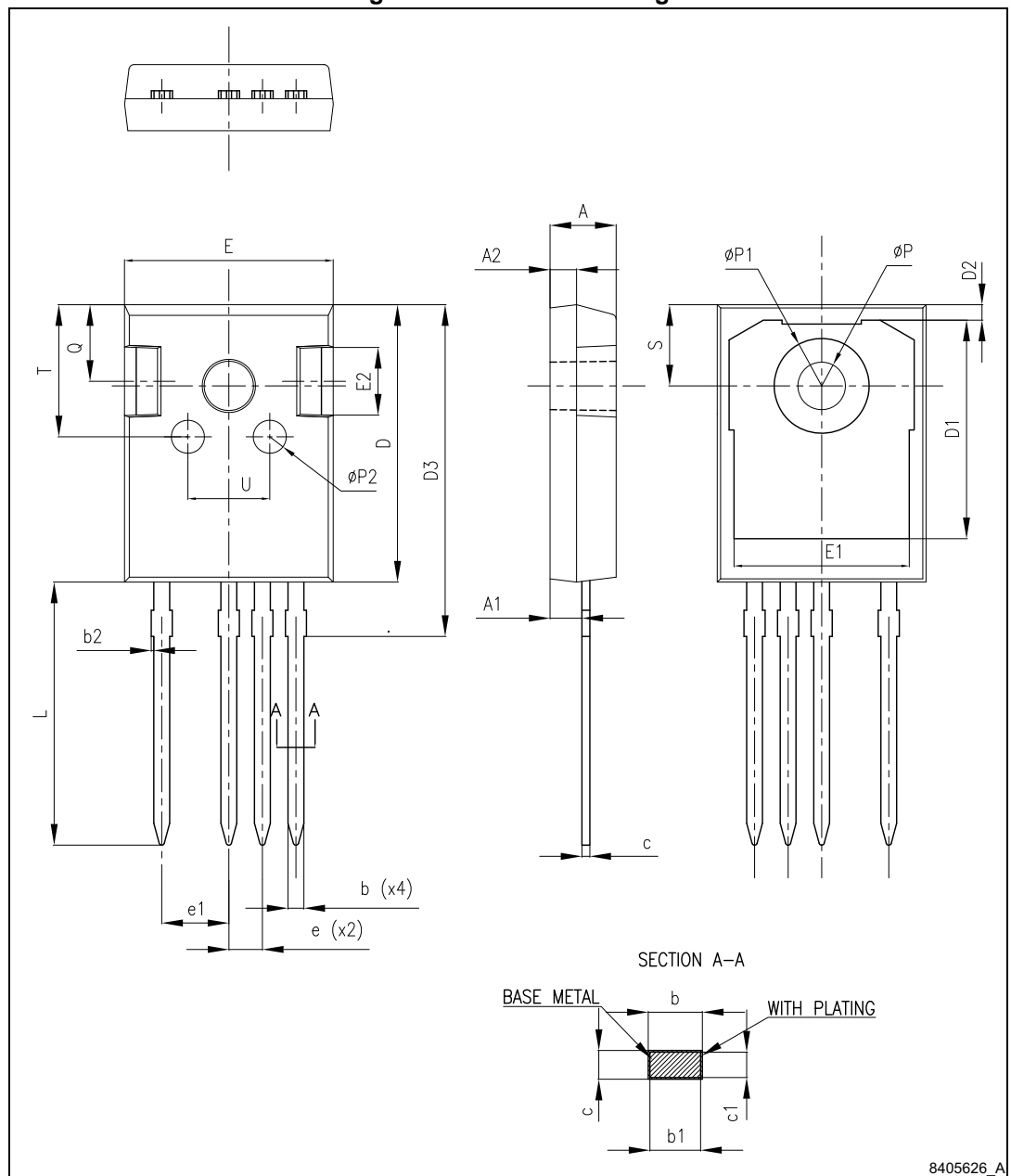


Table 9. TO247-4 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
b	1.16		1.29
b1	1.15	1.20	1.25
b2	0		0.20
c	0.59		0.66
c1	0.58	0.60	0.62
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	1.05	1.20	1.35
D3	24.97	25.12	25.27
E	15.70	15.80	15.90
E1	13.10	13.30	13.50
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e	2.44	2.54	2.64
e1	4.98	5.08	5.18
L	19.80	19.92	20.10
P	3.50	3.60	3.70
P1			7.40
P2	2.40	2.50	2.60
Q	5.60		6.00
S		6.15	
T	9.80		10.20
U	6.00		6.40

## 5 Revision history

Table 10. Document revision history

Date	Revision	Changes
15-Dec-2014	1	Initial release.

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